

November 2013

# FQPF3N25

# N-Channel QFET® MOSFET

250 V, 2.3 A, 2.2 Ω

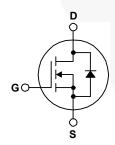
## **Description**

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply.

### **Features**

- 2.3 A, 250 V,  $R_{DS(on)}$  = 2.2  $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 1.15 A
- Low Gate Charge (Typ. 4.0 nC)
- Low Crss (Typ. 4.7 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF3N25	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		250	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		2.3	А	
	- Continuous (T <sub>C</sub> = 100°C)		1.45	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	9.2	A	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	40	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	2.3	А	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	2.7	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		27	W	
	- Derate above 25°C		0.22	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FQPF3N25	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.63	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF3N25	FQPF3N25	TO-220F	Tube	N/A	N/A	50 units

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		0.24		V/°C
I <sub>DSS</sub>	Zero Ceta Valta de Dueia Comuna	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.15 A		1.75	2.2	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 1.15 A		1.4		S
	ic Characteristics				ı	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		130	170	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		30	40	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			4.7	6.1	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 2.8 A,		6.6	23	ns
t <sub>r</sub>	Turn-On Rise Time	$R_{G} = 25 \Omega$		25	60	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			5.5	21	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		20	50	ns
Qg	Total Gate Charge	$V_{DS} = 200 \text{ V}, I_{D} = 2.8 \text{ A},$		4.0	5.2	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		1.1		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)	/	2.2		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				2.3	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	ode Forward Current			9.2	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.3 \text{ A}$			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.8 A,		100		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		0.3	//	μС

- **Notes:**1. Repetitive rating : pulse-width limited by maximum junction temperature.
  2. L = 12 mH,  $I_{AS}$  = 2.3 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C.
  3.  $I_{SD}$  ≤ 2.8 A, di/dt ≤ 300 A/ $\mu$ s,  $V_{DD}$  ≤ BV $_{DSS}$ , starting  $T_{J}$  = 25°C.
  4. Essentially independent of operating temperature.

# **Typical Characteristics**

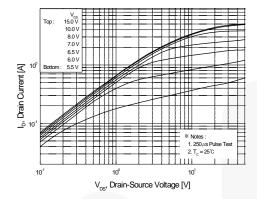


Figure 1. On-Region Characteristics

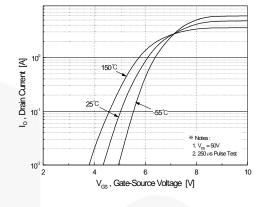


Figure 2. Transfer Characteristics

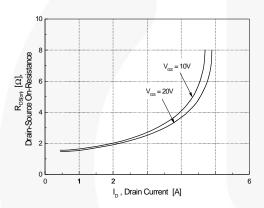


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

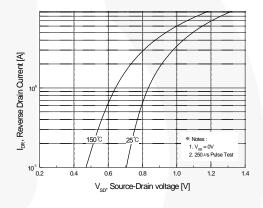


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

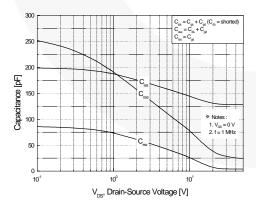


Figure 5. Capacitance Characteristics

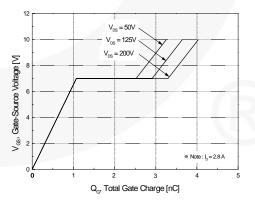


Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)

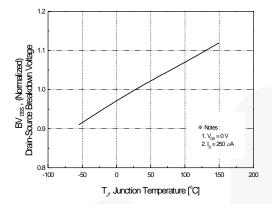


Figure 7. Breakdown Voltage Variation vs. Temperature

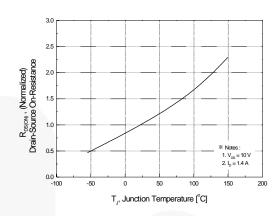


Figure 8. On-Resistance Variation vs. Temperature

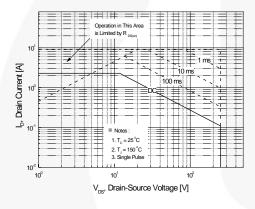


Figure 9. Maximum Safe Operating Area

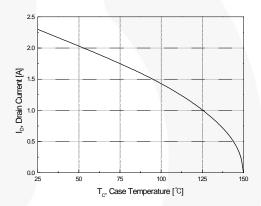


Figure 10. Maximum Drain Current vs. Case Temperature

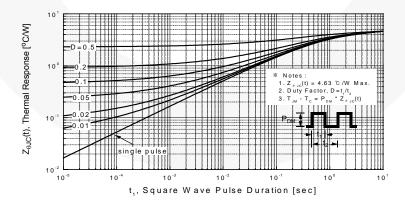


Figure 11. Transient Thermal Response Curve

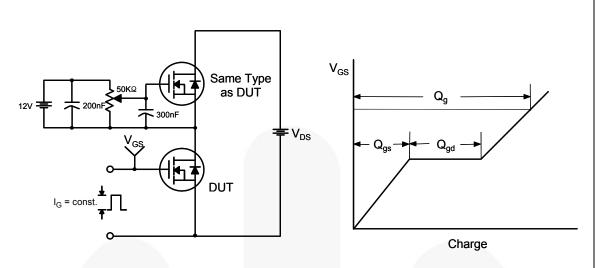


Figure 12. Gate Charge Test Circuit & Waveform

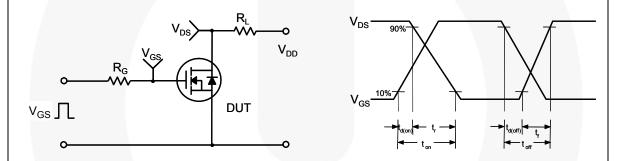


Figure 13. Resistive Switching Test Circuit & Waveforms

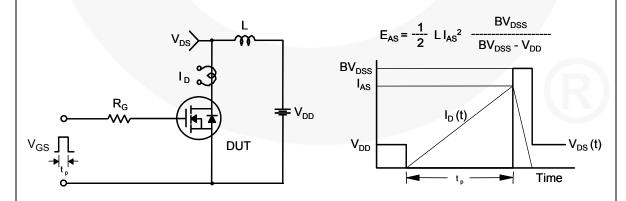
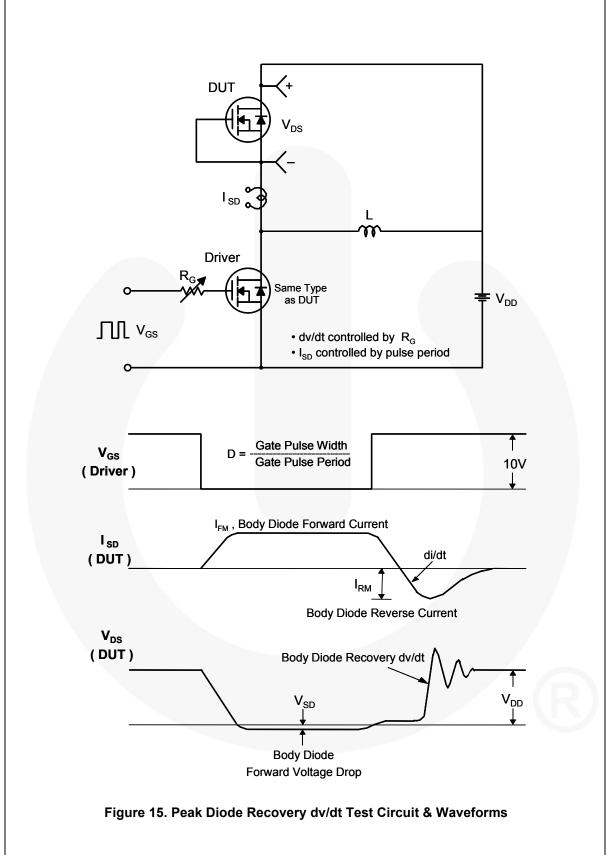


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

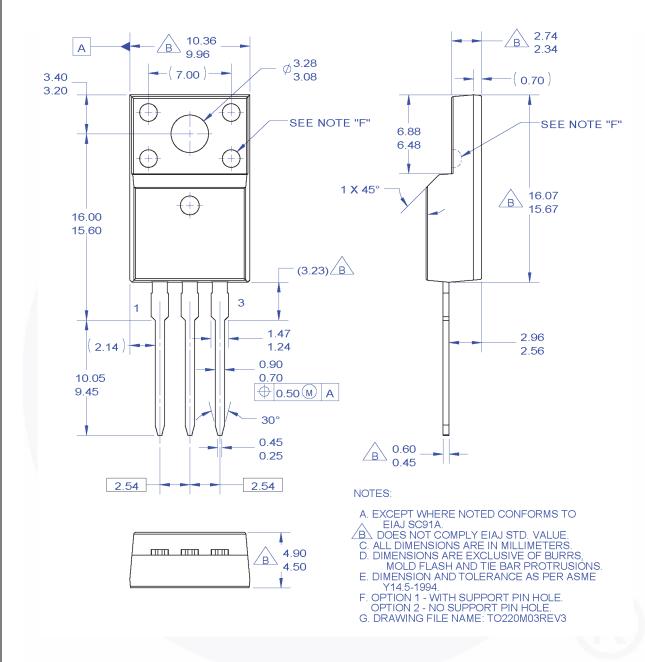


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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